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MQC-Fano effect in single molecule magnet transistors

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We consider the electron transport in single molecule magnet transistors in the presence of Zeeman spin splitting and magnetic quantum coherence (MQC). The Zeeman interaction is extended along the leads, thereby producing gaps in the energy spectrum which allow electron transport with spin polarized along a certain direction. The MQC induces an effective coupling between localized spin states and continuum spin states in the single molecule magnet and leads, respectively. We investigate the conductance at zero temperature as a function of the applied bias and magnetic field, and show that the MQC is responsible for the appearence of Fano resonances. Accordingly, we name them MQC-Fano resonances.

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Introduction. At present, the generation of spin polarized currents and its transmission through single molecule magnets (SMMs) is one of the most promising topics in spintronics. It is well known that ferromagnets are the natural sources of polarized electrons, and one can extract the polarized electrons using photo emission techniques. But there are some disadvantages for the ferromagnetic sources since to switch over the spin direction the inversion of the magnetization of the cathode is needed. This is where SMMs come into play. Single-molecule magnets, such as Mn_{12} (see Refs. 1, 2) and Fe_8 (see Refs. 3, 10), have become the focus of intense research since experiments on bulk samples demonstrated the magnetic quantum tunneling of a single magnetic moment on a macroscopic scale. These molecules are characterized by a large total spin, a large magnetic anisotropy barrier, and anisotropy terms which allow the spin to tunnel through the barrier. Macroscopic quantum coherence (MQC) is realized when the SMM tunnels several times between degenerate spin states with opposite spin projections on the magnetic easy axis before the coherence is destroyed by the environment. MQC requires a quantum tunneling rate that is large compared to the decoherence rate. Evidence of MQC has been reported for various superconducting systems and for antiferromagnetic nanoclusters. [4–9]

Electronic transport through SMMs offers several unique features with potentially large impact on applications such as high-density magnetic storage as well as quantum computing.[11] Recent experiments have pointed out the importance of the interference between spin tunneling paths in molecules. For instance, measurements of the magnetization in bulk Fe_8 have observed oscillations in the tunnel splitting $\Delta_{m,-m}$ between states $S_z = m$ and $-m$ as a function of a transverse magnetic field at temperatures between 0.05 K and 0.7 K (see Ref. 12, 13). This effect can be explained by the interference between Berry phases associated to spin tunneling paths of opposite windings.[14–18] More recently, there has been a renewed interest in the Fano resonance in connection with interference effects in quantum dots, quantum wires and mesoscopic transport phenomena.[19] The Fano resonance involves the mixing between a discrete state and one belonging to the continuum state.[20] The Fano resonance arises through the quantum interference of two transport pathways and manifests itself in the transmission probability.[21–23]

In the following, we investigate the electronic transport through a SMM transistor with Zeeman spin splitting and MQC. The Zeeman interaction is extended along the leads which produces gaps in the energy spectrum which allow electron transport with spin polarized along a certain direction. The MQC induces an effective coupling betwen localized spin states and continuum states in the molecular magnet and leads, respectively, creating the simplest scenario for the Fano resonance. We show that the MQC is responsible for opening a channel for the electron to tunnel through the single molecule magnet transistor. Moreover, the MQC-Fano effect may be fine-tuned using a longitudinal magnetic field, thereby providing a new method to observe the coherent spin tunneling indirectly through the Fano resonance. Expressions for the conductance through a SMM transistor for both zero and finite bias as a function of the applied magnetic field is calculated by means of the Landauer formalism at zero temperature for the SMM Ni_4.

Model Hamiltonian. The total Anderson-type Hamiltonian of a system formed by a single-molecule magnet (SMM) attached to two metallic leads can be separated into three terms (see Fig. 1),

$$\mathcal{H}_{\text{tot}} = \mathcal{H}_{\text{SMM}} + \mathcal{H}_{\text{lead}} + \mathcal{H}_{\text{SMM-lead}}. \tag{1}$$

The first term on the right-hand side of Eq. (1) denotes the SMM part, which can be broken into spin, charging, and gate contributions,

$$\mathcal{H}_{\text{SMM}} = \mathcal{H}^{(q)}_{\text{spin}} + E_c - q\,eV_g, \tag{2}$$

where E_c denotes the charging energy, q is the number of excess electrons (the charge state of the molecule), and V_g is the electric potential due to an external gate voltage. In the presence of an external magnetic field, the spin Hamiltonian of the SMM reads

$$\begin{aligned}\mathcal{H}_{\rm spin}^{(q)} &= -A_q S_{q,z}^2 + \frac{B_{2,q}}{2}\left(S_{q,+}^2 + S_{q,-}^2\right) \\ &+ \frac{B_{4,q}}{3}\left(S_{q,+}^4 + S_{q,-}^4\right) \\ &+ \frac{1}{2}\left(h_\perp^* S_{q,+} + h_\perp S_{q,-}\right) + h_\parallel S_{q,z}, \qquad (3)\end{aligned}$$

where the easy axis is taken along the z direction and $S_{q,\pm} = S_{q,x} \pm i S_{q,y}$. The magnetic field components were rescaled to $h_\perp = g\mu_B(H_x + iH_y)$ and $h_\parallel = g\mu_B H_z$ for the transversal and longitudinal parts, respectively, where g denotes the electron gyromagnetic factor. Note that the transverse magnetic field lies in the xy plane. In this Hamiltonian, the dominant longitudinal anisotropy term creates a ladder structure in the molecule spectrum where the $|\pm m_q\rangle$ eigenstates of $S_{q,z}$ are degenerate. The transverse anisotropy term lifts the degeneracy, creating an energy gap between spin states $|\pm m_q\rangle$ denoted by $\Delta_{mm'}$. The total spin as well as the coupling parameters depend on the charging state of the molecule. For example, it is known that Mn$_{12}$ changes its easy-axis anisotropy constant (and its total spin) from $A_0 = 56$ μeV ($S_{q=0} = 10$) to $A_{-1} = 43$ μeV ($S_{q=-1} = 19/2$) and $A_{-2} = 32$ μeV ($S_{q=-2} = 10$) when singly and doubly charged, respectively.[24] We will consider the leads as a one dimensional linear chain of sites. Thus, the second term on the right-hand side of Eq. (1) is given by,

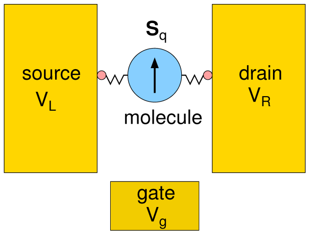

FIG. 1: Schematic illustration of a single-molecule field-effect transistor formed by a single-molecule magnet attached to two leads and controlled by a back gate voltage.

$$\mathcal{H}_{\rm lead} = \sum_i \sum_{\sigma=\uparrow,\downarrow} \epsilon_\sigma c_{i\sigma}^\dagger c_{i\sigma} - v \sum_{\langle i\neq j\rangle} \sum_{\sigma=\uparrow,\downarrow} \left(c_{i\sigma}^\dagger c_{j\sigma} + c_{j\sigma}^\dagger c_{i\sigma}\right), \qquad (4)$$

where the operator $c_{i\sigma}^\dagger$ ($c_{i\sigma}$) creates (annihilates) electronic states in the leads with spin orientation $\sigma =\uparrow,\downarrow$, and energy ϵ_σ. The potential of the wire is taken to be zero and the hopping in the wire is v. The on site energies in the leads and in the SMM are given by $\epsilon_\sigma = \frac{\Delta_Z}{2}[\sigma_z]_{\sigma\sigma}$ and $\varepsilon_{0\sigma}$, respectively. $\Delta_Z = g\mu_B H_z$ is the Zeeman energy splitting in the leads and σ_z is the Pauli matrix.[25] Denoting $\lambda_{s,-s}$ as the coupling matrix element between the states $|s\rangle$ and $|-s\rangle$, we obtain the following effective Hamiltonian for the interaction of the SMM with the leads:

$$\begin{aligned}\mathcal{H}_{\rm SMM-lead} &= t\Big(\left|s'\right\rangle\left\langle s\right| c_{1\downarrow} + c_{1\downarrow}^\dagger \left|s\right\rangle\left\langle s'\right| \\ &\quad + \left|-s'\right\rangle\left\langle -s\right| c_{1\uparrow} + c_{1\uparrow}^\dagger\left|-s\right\rangle\left\langle -s'\right|\Big) + \\ &\quad t\Big(\left|s'\right\rangle\left\langle s\right| c_{-1\downarrow} + c_{-1\downarrow}^\dagger\left|s\right\rangle\left\langle s'\right| \\ &\quad + \left|-s'\right\rangle\left\langle -s\right| c_{-1\uparrow} + c_{-1\uparrow}^\dagger\left|-s\right\rangle\left\langle -s'\right|\Big) + \\ &\quad \lambda_{s',-s'}\left(\left|-s'\right\rangle\left\langle s'\right| + \left|s'\right\rangle\left\langle -s'\right|\right) + \\ &\quad \lambda_{s,-s}\left(\left|-s\right\rangle\left\langle s\right| + \left|s\right\rangle\left\langle -s\right|\right). \qquad (5)\end{aligned}$$

where t is the lead-molecule tunneling amplitude and λ is the magnetic quantum tunneling which is the source of splin flipping. The stationary states of the total Hamiltonian can be written as

$$|\psi_{\pm s'}\rangle = \sum_{j=-\infty, j\neq 0}^{\infty} a_{j,\pm s}|j\rangle|\pm s\rangle + b_{\pm s'}|0\rangle|\pm s'\rangle, \qquad (6)$$

where $a_{j,\pm s}$ and $b_{\pm s'}$ are the probability amplitudes to find the electron at the site $j \neq 0$ or at the SMM site $j = 0$, respectively, with energy $\omega = \epsilon_{-s'} - 2v\cos(k)$ or $\omega = \epsilon_{s'} - 2v\cosh(\kappa)$. Substituting Eq. (6) into the Hamiltonian we obtain the following linear difference equations:

$$\begin{aligned}(\omega - \epsilon_{\pm s'})a_{j,\pm s} &= -v(a_{j+1,\pm s} + a_{j-1,\pm s}),\ j \neq -1, 0, \qquad (7)\\ (\omega - \epsilon_{\pm s'})a_{-1,\pm s} &= -va_{-2,\pm s} - tb_{\pm s'}, \\ (\omega - \epsilon_{\pm s'})a_{1,\pm s} &= -va_{2,\pm s} - tb_{\pm s'}, \\ (\omega - \varepsilon_{0,\pm s})b_{\pm s'} &= -t(a_{1,\pm s} + a_{-1,\pm s}) - \lambda_{\pm s',\mp s'}b_{\mp s'}.\end{aligned}$$

We now focus on an energy range close to the band bottom, i.e. $-2v - \Delta_Z/2 \leq E \leq -2v + \Delta_Z/2$. Then, the eigenfunctions corresponding to spin $\downarrow$ ($\uparrow$) are propagating (evanescent) waves. In order to obtain the solution of the above equations we assumed that the spin-down electrons are described by plane waves with unitary incident amplitude coming from the left, with r and τ being the reflection and transmission amplitudes; therefore

$$\begin{aligned}a_{j,-s} &= e^{ikj} + re^{-ikj}, \quad j < 0, \qquad (8)\\ a_{j,-s} &= \tau e^{ikj}, \quad j > 0, \\ a_{j,s'} &= Ae^{\kappa j}, \quad j < 0 \\ a_{j,s'} &= Be^{-\kappa j}, \quad j > 0.\end{aligned}$$

Operating with the Hamiltonian on the state given in Eq. (8) we obtain the following linear difference equations

$$\begin{aligned}\lambda_{s',-s'}\beta e^{ik} &= A\left[t^2e^{-\kappa} - (\omega - \epsilon_{0,s'})\alpha e^{-\kappa}\right] \qquad (9)\\ &\quad + B\left[t^2 e^{-\kappa}\right] + r\left[\lambda_{s',-s'}\beta e^{ik}\right], \\ -t^2e^{-ik} + (\omega - \epsilon_{0,-s})\beta e^{ik} &= -A\left[\alpha e^{-\kappa}\right] + \tau\left[t^2 e^{ik}\right] \qquad (10)\\ &\quad + r\left[t^2e^{ik} - (\omega - \epsilon_{0,-s})\beta e^{ik}\right], \\ -t^2e^{-ik} &= -B\left[\lambda_{-s',s'}\alpha e^{-\kappa}\right] + r\left[t^2e^{ik}\right] \qquad (11)\\ &\quad + \tau\left[t^2e^{ik} - (\omega - \epsilon_{0,-s})\beta e^{ik}\right], \\ 0 &= A\left[t^2e^{-\kappa}\right] + B\left[t^2e^{-\kappa} - (\omega - \epsilon_{0,s'})\alpha e^{-\kappa}\right] \qquad (12)\\ &\quad + \tau\left[\lambda_{s',-s'}\beta e^{ik}\right],\end{aligned}$$

where

$$\alpha = ve^{-\kappa} - (\omega - \epsilon_{s'}), \quad \text{and} \quad \beta = ve^{ik} - (\omega - \epsilon_{-s'}). \quad (13)$$

Results. The conductance for the electron tunneling across the SMM transistor is calculated by means of the Landauer formalism at zero temperature, i.e.

$$G = \frac{e^2}{h} T(E_F), \quad (14)$$

where e is the charge unit and h is the Planck constant. The transmission probability at $\omega = E_F = 0$ is obtained by solving the inhomogeneous system of equations for τ given above. In what follows we present our results for the conductance for $\Delta_Z = 0.1v$, $k_F = \cos^{-1}(1 - \Delta_Z/4v)$ and $\kappa_F = \cosh^{-1}(1 + \Delta_Z/4v)$, where $G_0 = e^2/h$. We illustrate our findings with the SMM Ni$_4$, which has a total spin $S = 4$ and we propose as a possible candidate for the experimental observation of the MQC-Fano effect. Our motivation for studying this particular nanomagnet stems partly from its high symmetry (S4) but, more importantly, from the large tunnel splittings. The spin Hamiltonian for Ni$_4$ is to first approximation[26]

$$\mathcal{H}^{(q)}_{\text{spin}} = -DS_z^2 + C(S_+^4 + S_-^4) - \mu_B g H_Z S_Z, \quad (15)$$

where $D = 0.75$ K, $C = 2.9 \times 10^{-4}$ K, and $g = 2.3$. The off-diagonal terms in the Hamiltonian (15) lead to an energy splitting $\Delta_{mm'}$ between the two lowest energy levels. The large C-value is the reason for the fast ground state tunneling ($\Delta_{mm'} \approx 0.01$ K) observed at zero field, corresponding to an angular frequency of $\omega_T \approx 1$ GHz [27]. The external magnetic field H_z, applied along the easy axis of the SMM tilts the double well potential favoring those spin projections aligned with the field. To take advantage of the large ground state tunnel splitting we need to add a single electron to the nanomagnet in order to switch the total spin from $|4\rangle$ to $|9/2\rangle$ or $|7/2\rangle$. The final state is the result of the exchange interaction between the total spins in the nanomagnet. When the nanomagnet is singly charged the SMM will only allow electrons with spin down (up) polarization in single electron tunneling transport due to spin blockade. If the charged SMM has a spin ground state $|7/2\rangle$, then the transitions from $|7/2\rangle$ to $|4\rangle$ and from $|-7/2\rangle$ to $|-4\rangle$ are accompanied by the absorption of a spin up and spin down electron, respectively. In order to obtain sequential tunneling through $|-4\rangle$, the state $|-4\rangle$ must lie between the chemical potentials of the left and right leads, as indicated by the red regions in Fig. 2(a). If the charged SMM has a spin ground state $|9/2\rangle$, then the transitions from $|9/2\rangle$ to $|4\rangle$ and from $|-9/2\rangle$ to $|-4\rangle$ are accompanied by the absorption of a spin down and spin up electron as depicted in Fig. 2(b). The difference between $s = 9/2$ and $s = 7/2$ is that a different gate voltage V_g needs to be applied, in order to obtain sequential tunneling through the state $|-4\rangle$ of the SMM. For $s = 9/2$ spin up electrons are transmitted through the SMM, whereas for $s = 7/2$ spin down electrons are transmitted through the SMM. Figure (2) displays a schematic diagram of how the electron tunnels through the SMM transistor. The electron with spin down (up) can tunnel directly through the level $|-4\rangle$ without quantum tunneling of the magnetization or also can tunnel indirectly through $|-4\rangle \rightarrow |4\rangle \rightarrow |-4\rangle$ with two quantum tunneling processes, i.e. macroscopic quantum coherence. The interference between the two tunneling trajectories gives rise to the MQC-Fano effect presented in this article.

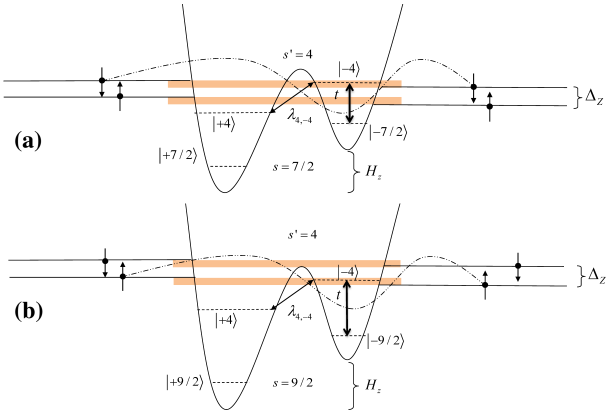

FIG. 2: Schematic illustration of tunneling through the SMM transistor for $s = 7/2$ and $s = 9/2$. The dotted line corresponds to the direct electron path across the SMM transistor. The quantum tunneling of the magnetization opens a new channel that interferes with the direct channel which produces the MQC-Fano interference.

We are going to consider an effective two level system with eigenvalues $\varepsilon_{0\sigma} = \varepsilon_0 + \sqrt{(\mu_B g H_z)^2 + \Delta^2_{mm'}}[\sigma_z]_{\sigma\sigma}/2$, where ε_0 is the energy level of the SMM without a magnetic field and $\Delta_{mm'} = 2\lambda_{m,-m}$. In all subsequent calculations we will express energy in temperature units. Therefore, a magnetic field $H_z = 1$ T is equal to $h_{\|} = 1.34$ K and 1 K is equal to a frequency of $\omega = 1.31 \times 10^{11}$ Hz. In Figure (3) the spin-dependent conductance versus the gate voltage is depicted for different values of the MQC interaction at a fixed longitudinal magnetic field of $h_{\|} = 0.23$ K. The conductance shows two resonances as a function of the Fermi energy. Note how the MQC-Fano effect is enhanced when the quantum tunneling coupling interaction is larger, i.e. high transition rates. This result shows that the conductance through the SMM transistor depends on the MQC. Interestingly, if the MQC coupling decreases there is no Fano resonance. The spin-dependent conductance versus the gate voltage is displayed in Fig. (4) for various values of the magnetic field in the SMM. Notice that the magnetic field modulates the spin-dependent conductance, allowing for a fine-tuning of the system response.

Conclusions. We have investigated electron transport through a single molecule magnet transistor with Zeeman spin splitting and magnetic quantum tunneling. We have shown that the transport through the SMM transistor exhibits a Fano resonance due to the coupling between bound levels of spin polarized electrons in the single molecule magnet with spin polarized electrons in the leads. This results provide a new method to observe the coherent spin tunneling (MQC) through

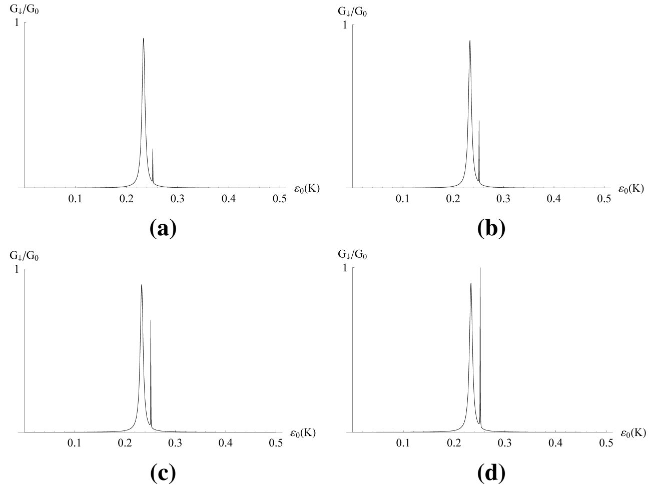

FIG. 3: Plots showing the spin-dependent conductance as a function of the gate voltage for different values of the coupling matrix element $\lambda_{s',-s'}$ i.e. (a) $\lambda_{s',-s'} = 0.007$ K, (b) $\lambda_{s',-s'} = 0.008$ K, (c) $\lambda_{s',-s'} = 0.009$ K and (d) $\lambda_{s',-s'} = 0.01$ K, with a constant magnetic field of $h_{\parallel} = 0.23$ K. Note how the MQC-Fano effect increases with the coupling interaction.

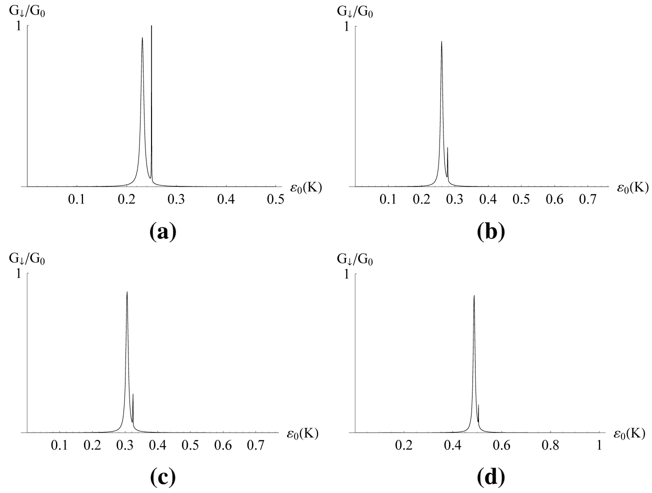

FIG. 4: Plots showing the spin-dependent conductance as a function of the gate voltage for different values of the magnetic field: (a) $h_{\parallel} = 0.23$ K, (b) $h_{\parallel} = 0.45$ K, (c) $h_{\parallel} = 0.75$ K and (d) $h_{\parallel} = 1$ K, with a fixed quantum tunneling coupling, i.e. $\lambda_{s',-s'} = 0.01$ K. Note that the MQC-Fano effect can be tuned by means of the applied external magnetic field.

Fano resonances of the spin dependent conductance as a function of the gate voltage and of the magnetic field applied in the single molecule magnet. We propose to use the single molecule magnet Ni_4 for the experimental observation of this phenomenon.

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